


Amendments to the Claims

The claims have been amended as follows. Underlines indicate insertions and ~~strikeouts~~ indicate deletions.

Claims 1-50 (Cancelled).

51. (Currently amended) A method of forming a bottom-gated thin film transistor comprising the following steps:

 . forming a transistor gate;
forming a polycrystalline thin film transistor layer over the transistor gate;
forming a fluorine-containing layer proximate the polycrystalline thin film transistor layer, the fluorine-containing layer comprising tungsten; and
transferring fluorine into the polycrystalline thin film transistor layer from the fluorine-containing layer, the transferred fluorine passivating the polycrystalline thin film transistor layer in the bottom-gated thin film transistor.

52. (Previously presented) The method of claim 51 wherein the polycrystalline thin film transistor layer comprises silicon.

53. (Previously presented) The method of claim 51 wherein the forming a fluorine-containing layer comprises chemical vapor deposition utilizing WF_6 and SiH_4 precursors.

54. (Previously presented) The method of claim 53 further comprising, after the transferring fluorine, removing the fluorine-containing layer from over the thin film transistor layer.

55. (Previously presented) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine-containing layer over the transistor gate and over the polycrystalline thin film transistor layer;

providing a buffering layer intermediate the thin film transistor layer and the fluorine-containing layer; and

transferring fluorine into the polycrystalline thin film transistor layer over the transistor gate from the fluorine-containing layer.

56. (Previously presented) The method of claim 55 wherein the fluorine-containing layer comprises tungsten.

57. (Previously presented) The method of claim 55 wherein the buffering layer comprises SiO₂.

58. (Previously presented) The method of claim 55 wherein the polycrystalline thin film transistor layer comprises germanium.